ON Semiconductor

Is Now

Onsemi

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Amplifier Transistors

PNP Silicon

Features

• These are Pb-Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	-50	Vdc
Collector-Base Voltage	V _{CBO}	-60	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	۱ _C	-100	mAdc
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	350 2.8	mW mW/°C
Total Device Dissipation @ $T_C = 25^{\circ}C$ Derate above $25^{\circ}C$	PD	1.0 8.0	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

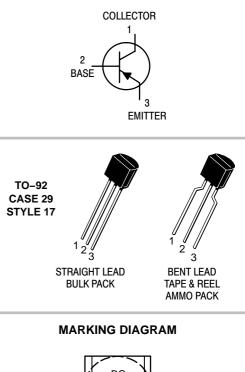
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	125	°C/W

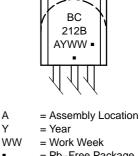
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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А

Υ

= Pb-Free Package (Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BC212BG	TO–92 (Pb–Free)	5000 Units / Bulk
BC212BRL1G	TO–92 (Pb–Free)	2000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

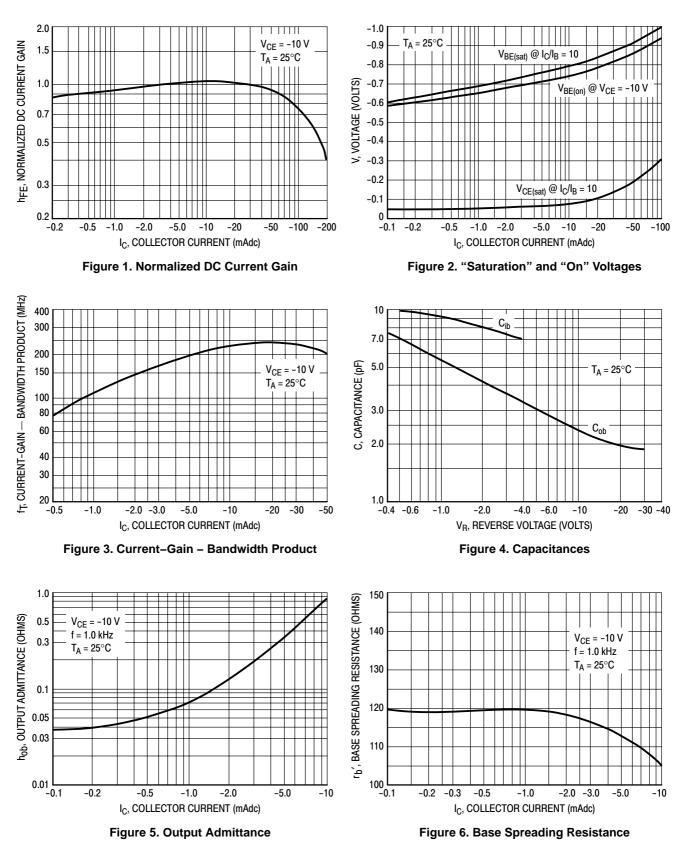
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BC212B

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Collector – Emitter Breakdown Voltage	V _{(BR)CEO}	-50	-	-	Vdc
Collector – Base Breakdown Voltage	V _{(BR)CBO}	-60	-	-	Vdc
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5	-	-	Vdc
Collector-Emitter Leakage Current	I _{CBO}	-	-	-15	nAdc
Emitter-Base Leakage Current	I _{EBO}	-	-	-15	nAdc
ON CHARACTERISTICS					
DC Current Gain (I _C = −10 μAdc, V _{CE} = −5.0 Vdc)	h _{FE}	40	-	-	-
$(I_C = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$		60	-	-	
(I _C = -100 mAdc, V _{CE} = -5.0 Vdc) (Note 1)		-	120	_	
Collector – Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}, I_B = -0.5 \text{ mAdc}$) ($I_C = -100 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$) (Note 1)	V _{CE(sat)}		-0.10 -0.25	_ _0.6	Vdc
Base – Emitter Saturation Voltage ($I_C = -100$ mAdc, $I_B = -5.0$ mAdc)	V _{BE(sat)}	-	-1.0	-1.4	Vdc
Base–Emitter On Voltage ($I_C = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}$)	V _{BE(on)}	-0.6	-0.62	-0.72	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain – Bandwidth Product ($I_C = -10 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}, f = 100 \text{ mHz}$)	f _T	-	280	_	MHz
Common-Base Output Capacitance ($V_{CB} = -10 \text{ Vdc}, I_C = 0, f = 1.0 \text{ mHz}$)	C _{ob}	_	-	6.0	pF
Noise Figure (I _C = -0.2 mAdc, V _{CE} = -5.0 Vdc, R _S = 2.0 kΩ, f = 1.0 kHz, f = 200 Hz)	NF	-	-	10	dB
Small–Signal Current Gain (I _C = –2.0 mAdc, V _{CE} = –5.0 Vdc, f = 1.0 kHz)	h _{fe}	200	-	400	-

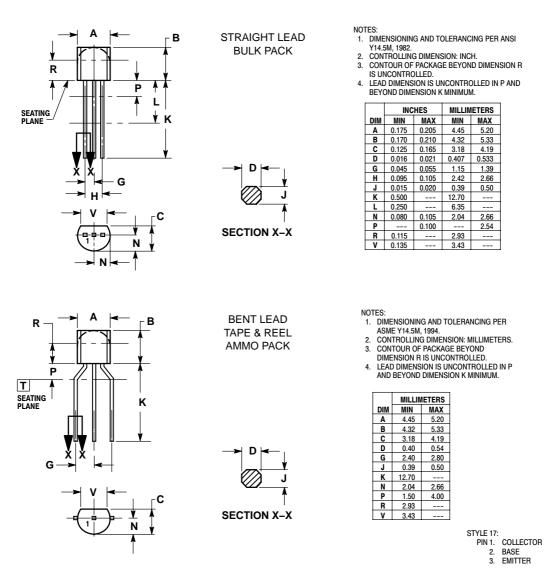
1. Pulse Test: Tp 300 s, Duty Cycle 2.0%.



BC212B

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



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